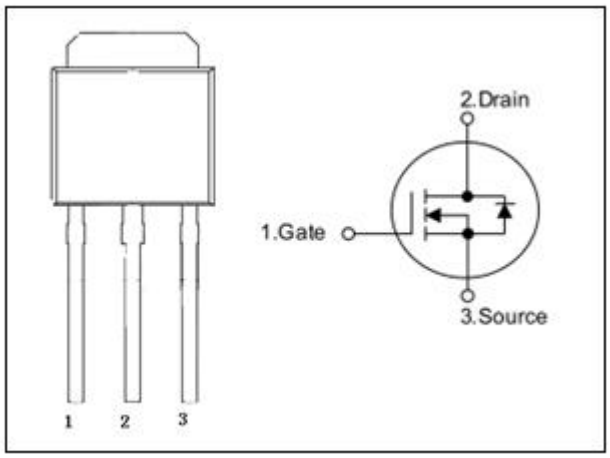
Isc N-Channel MOSFET Transistor MMIS70R900PTH

- **FEATURES**
- With TO-251(IPAK) packaging
- Low power loss
- High speed switching
- Low on-resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **APPLICATIONS**
- Switching applications
- DC － DC Converters

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	700	V
V_{GSS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous@T_C=25℃ T_C=100℃	5 3	A
I_{DM}	Drain Current-Single Pulsed	15	A
P_D	Total Dissipation	40	W
T_{ch}	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.1	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	700			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= ±30V; I_D=0.25mA	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=1.5A		810	900	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=700V; V_{GS}= 0V;			1	μA
V_{SDF}	Diode forward voltage	I_{SD}=5A, V_{GS} = 0 V			1.4	V

TO-251 OUTLINE DIMENSIONAL DRAWING